Product specification

 $1.3^{+0.1}_{-0.1}$

2 =



Unit: mm

0.1+0.05

Features

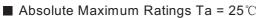
• Low VF and high efficiency.

TY Semicondutor[®]

 HSM107S which is interconnected in series configuration is designed for protection from not only external excessive voltage but also miss-operation on electric systems.

Т

• MPAK package is suitable for high density surface mounting and high speed assembly.



Parameter	Symbol	Value	Unit
Reverse voltage	Vr	8	V
Peak forward current	lfм	0.1	А
Non-Repetitive Peak forward surge current	IFSM (Note 1)	0.5	А
Average rectified current	lo	50	mA
Junction temperature	Tj	125	°C
Storage temperature	Tstg	-55 to +125	°C

Note

1. Square wave, 10ms

■ Electrical Characteristics Ta = 25°C

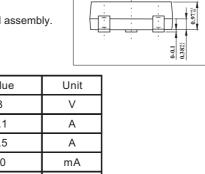
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Reverse voltage	Vr	VR =1.0 mA	8			pF
Reverse current	lr	Vr = 5 V			30	μA
Forward voltage	Vf	IF = 10 mA			0.3	V
ESD-Capability (Note 1)	C=200pF , Both forward and	100			V	
		reverse direction 1 pulse.	100			v

Note

1. Failure criterion ; IR \geq 60 $\,\mu$ A at VR =5 V

Marking

Marking C5



2.4^{-0.1}

SOT-23

2.9^{+0.1} 0.4^{+0.1}